Supporting Information

Excellent Stability of Thicker Shell CdSe@ZnS/ZnS Quantum Dots

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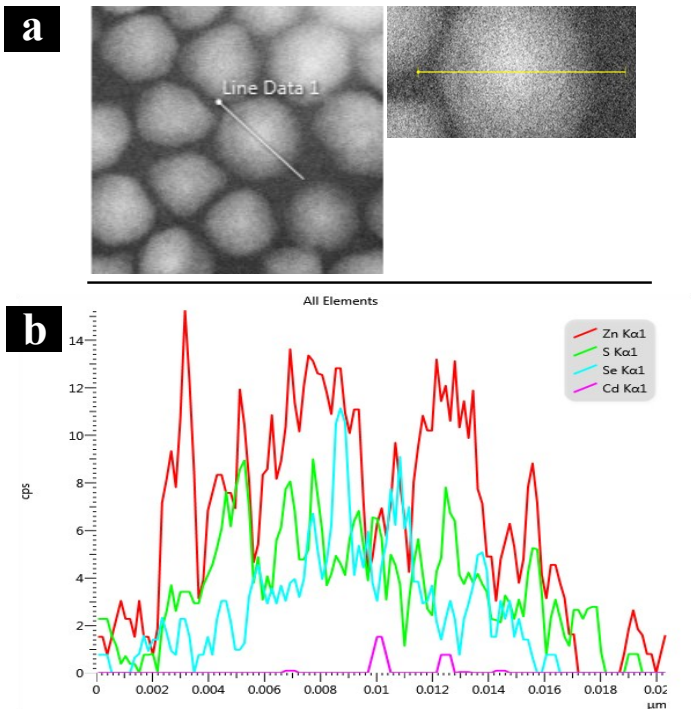

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QDs	9 nm	12 nm	13 nm	13.6 nm
Element	Atomic %			
S	35.73	49.64	47.8	46.64
Zn	43.4	37	41.73	43.22
Se	19.24	12.58	9.78	9.53
Cd	1.63	0.78	0.69	0.61
Total	100.00	100.00	100.00	100.00

Fig. S1. (a) TEM-EDS line scan along a single CdSe@ZnS A- QDs. (b) EDS mapping of CdSe@ZnS A- QDs_9 nm QDs. (c) The atomic percentage of each element of thick shell QDs is presented in table.

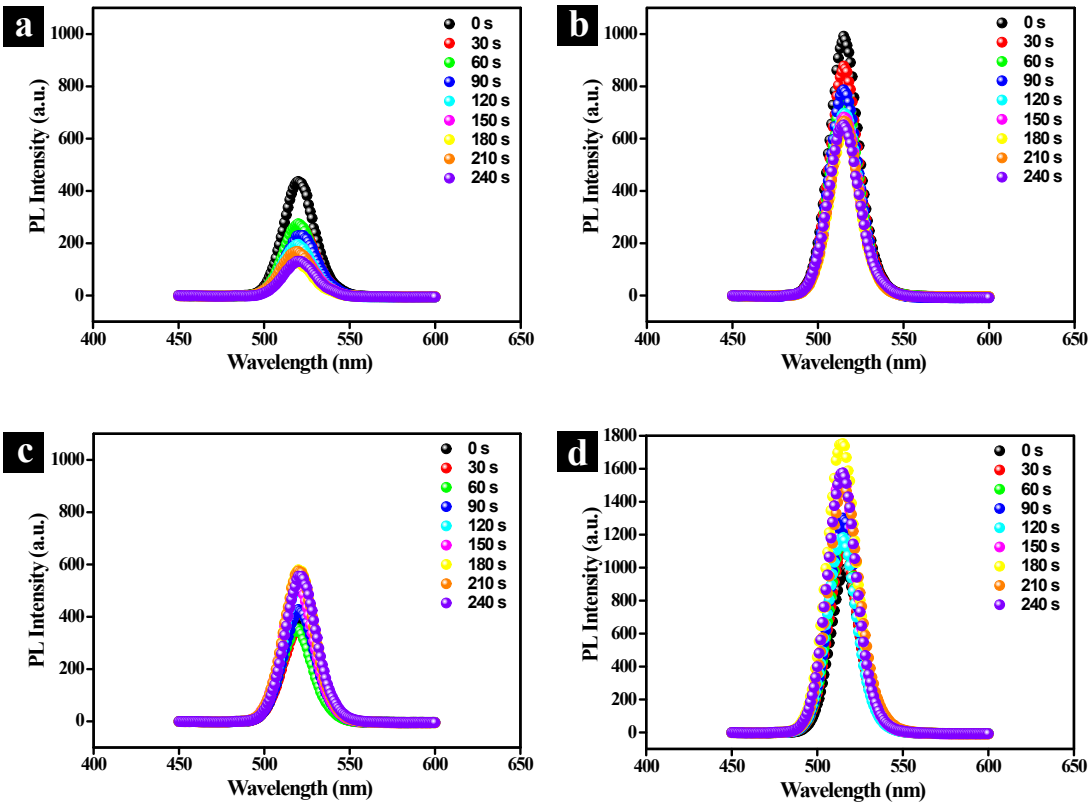

Fig. S2. Photochemical stability of the PL relative intensity of (a) A-QDs film under UV-irradiation exposure in O_2 environment; (b) AS-QDs film under UV-irradiation exposure in O_2 environment; (c) A-QDs film under UV-irradiation exposure in air environment; (d) AS-QDs film under UV-irradiation exposure in air environment.